

Silicon NPN Power Transistors

BUT11F BUT11AF

DESCRIPTION

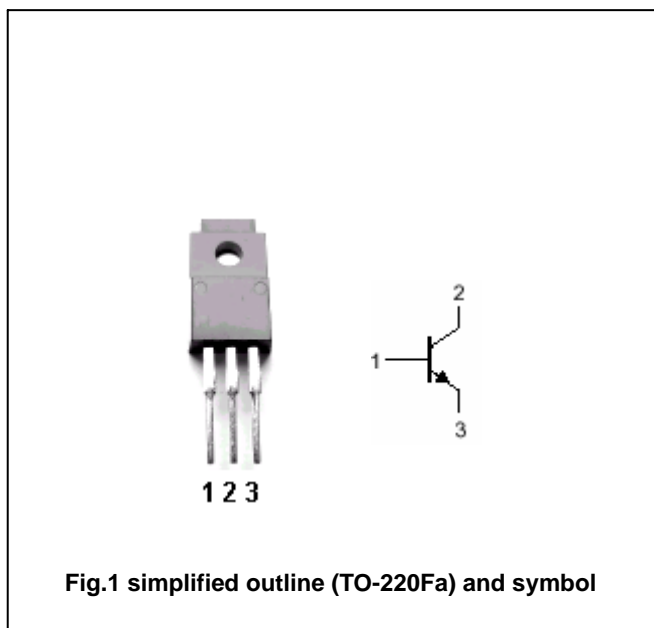
- With TO-220Fa package
- High voltage ,high speed

APPLICATIONS

- Converters
- Inverters
- Switching regulators
- Motor control systems

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings (Tc=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	BUT11F	850	V
		BUT11AF	1000	
V _{CEO}	Collector-emitter voltage	BUT11F	400	V
		BUT11AF	450	
V _{EBO}	Emitter-base voltage	Open collector	9	V
I _C	Collector current		5	A
I _{CM}	Collector current-peak		10	A
I _B	Base current		2	A
I _{BM}	Base current-peak		4	A
P _{tot}	Total power dissipation	T _C =25	40	W
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-65~150	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R _{th j-c}	Thermal resistance from junction to case	3.125	K/W

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CHARACTERISTICS

Tj=25 unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	BUT11F	I _C =0.1A; I _B =0	400			V
		BUT11AF		450			
V _{CEsat}	Collector-emitter saturation voltage	BUT11F	I _C =3A; I _B =0.6A			1.5	V
		BUT11AF	I _C =2.5A; I _B =0.5A				
V _{BEsat}	Base-emitter saturation voltage	BUT11F	I _C =3A; I _B =0.6A			1.3	V
		BUT11AF	I _C =2.5A; I _B =0.5A				
I _{CES}	Collector cut-off current	BUT11F	V _{CE} =850V ; V _{BE} =0			1.0	mA
		BUT11AF	V _{CE} =1000V ; V _{BE} =0				
I _{EBO}	Emitter cut-off current		V _{EB} =9V; I _C =0			10	mA
h _{FE-1}	DC current gain		I _C =5mA ; V _{CE} =5V	10		35	
h _{FE-2}	DC current gain		I _C =0.5A ; V _{CE} =5V	10		35	
Switching times resistive load							
t _{on}	Turn-on time		I _C =2.5A; I _{B1} =- I _{B2} =0.5A V _{CC} =250V; R _L =100			1.0	μs
t _s	Storage time					4.0	μs
t _f	Fall time					0.8	μs

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PACKAGE OUTLINE

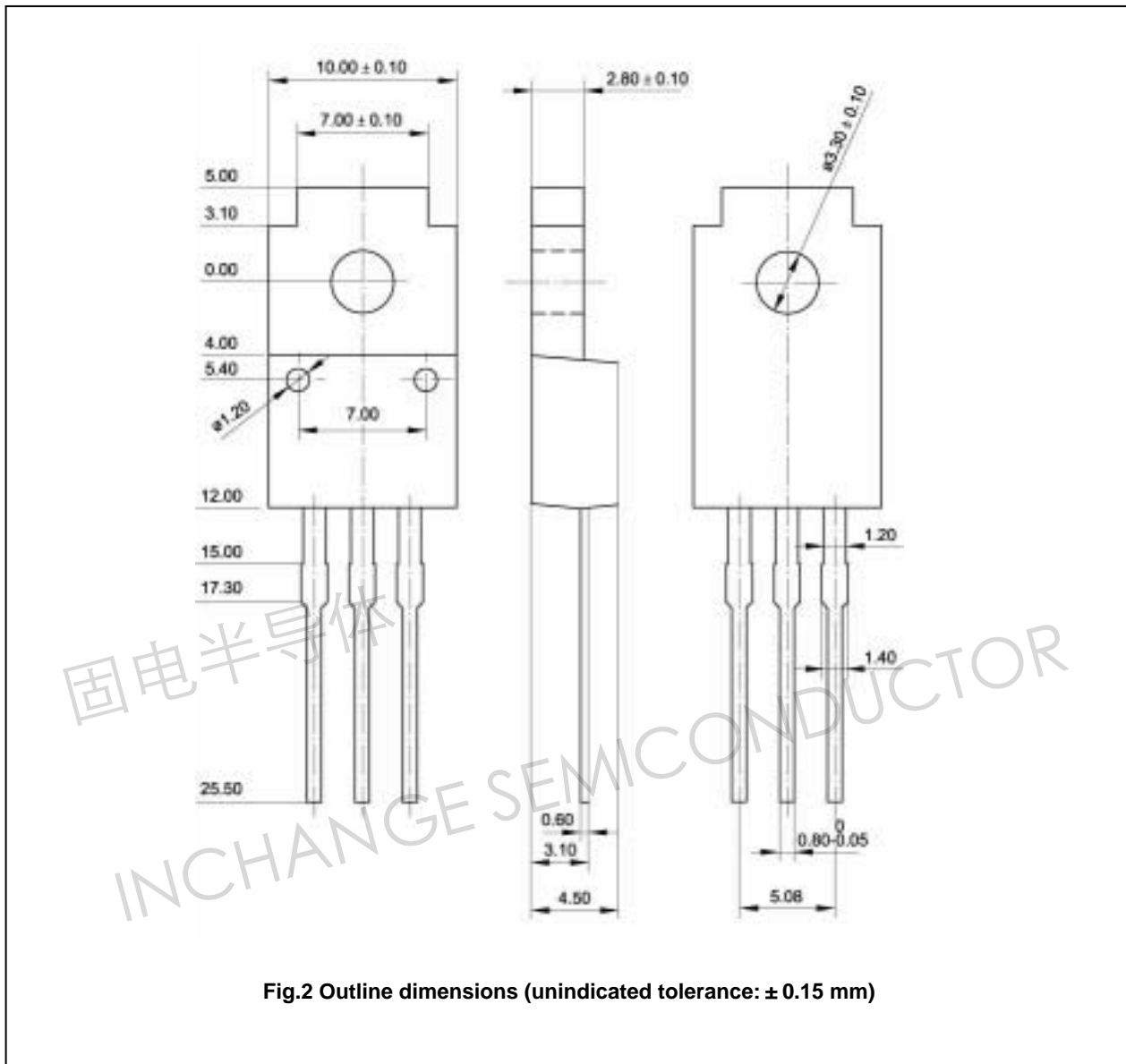


Fig.2 Outline dimensions (unindicated tolerance: ± 0.15 mm)